FEATURES

- Red to Near Infrared Enhanced Photodiode
- Photosensitive Active Area: 1 mm x 1 mm
- High Sensitivity: 0.62 A/W (ʎ = 850 nm), 0.35 A/W ʎ = 1064 nm)
- Wide Operating Temperature: -40°C to +125°C
- Ideal for Laser Monitoring Applications
- RoHS and REACH Compliant

Electro-Optical Characteristics at 25°C

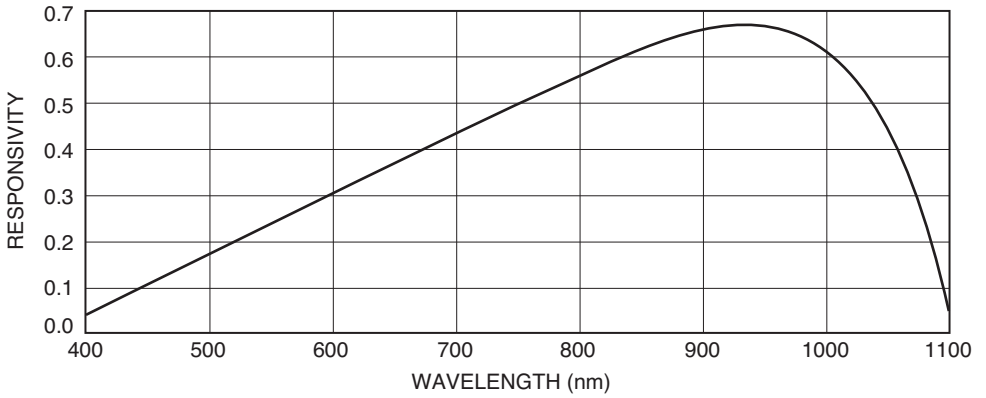
Parameters	Test Conditions	Min	Typ	Max	Units
Active Area			1		mm^2
Spectral Response Range, λ		320		1100	nm
Responsivity	@ 850 nm		0.62		A/W
Responsivity	@ 1064 nm		0.35		A/W
Dark Current, Idr	Vr = 3 V		0.1	0.75	nA
Shunt Resistance	V_R = 10 mV	200	500		MΩ
Reverse Breakdown Voltage, V_R	I_R = 1 µA	50			Volts
Capacitance, C	V_R = 0 V		3		pF
Rise Time	V_R = 5 V		50		nsec

Thermal Parameters

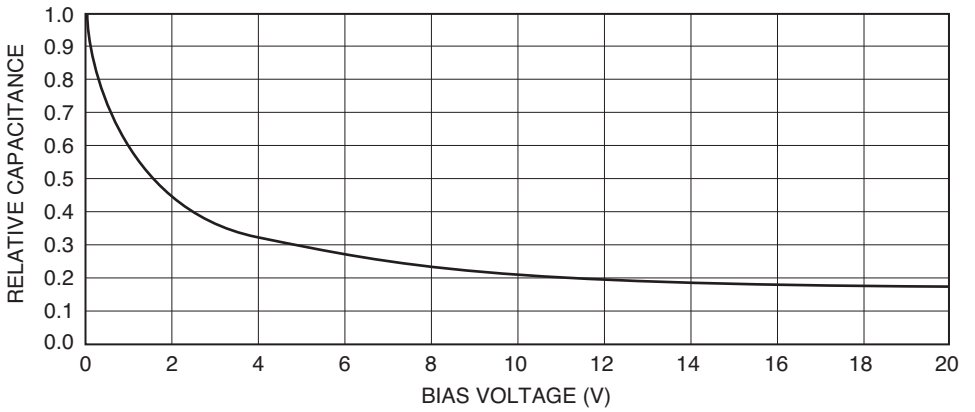
Parameters	Units
Storage and Operating Temperature Range	-40°C to 125°C
Maximum Junction Temperature	125°C

APTechnologies
www.aptechnologies.co.uk
AP Technologies Limited The Coach House Watery Lane Bath BA2 1RL
T: +44 (0) 1225 780400 F: +44 (0) 8701 266449 E: info@aptechnologies.co.uk

Typical Spectral Response



Capacitance vs Bias Voltage



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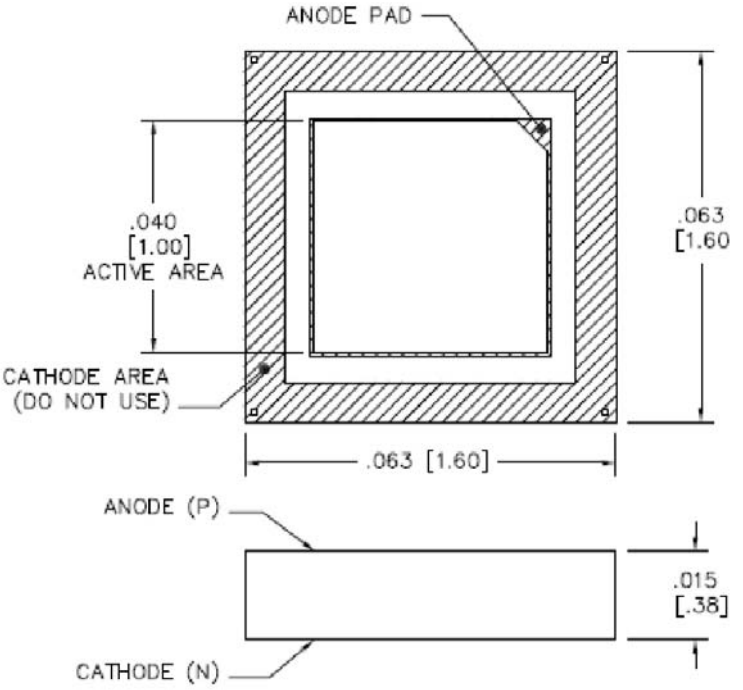
Package Dimensions



Specifications are subject to change without prior notice.